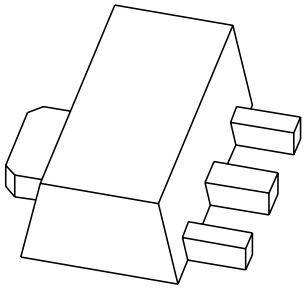
DATA SHEET



PXT2907A
PNP switching transistor

Product specification
Supersedes data of 1999 Apr 14

2002 Mar 20

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PNP switching transistor PXT2907A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 60 V).

APPLICATIONS

- Switching and linear amplification.

DESCRIPTION

PNP switching transistor in a SOT89 plastic package.
NPN complement: PXT2222A.

MARKING

TYPE NUMBER	MARKING CODE
PXT2907A	p2F

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base

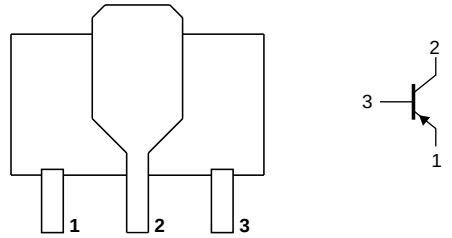


Fig.1 Simplified outline (SOT89) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–60	V
V_{CEO}	collector-emitter voltage	open base	–	–60	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–600	mA
I_{CM}	peak collector current		–	–800	mA
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	1.3	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 6 cm^2.
   For other mounting conditions, see *"Thermal considerations for SOT89 in the General Part of associated Handbook".*

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	97	K/W
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point		17	K/W

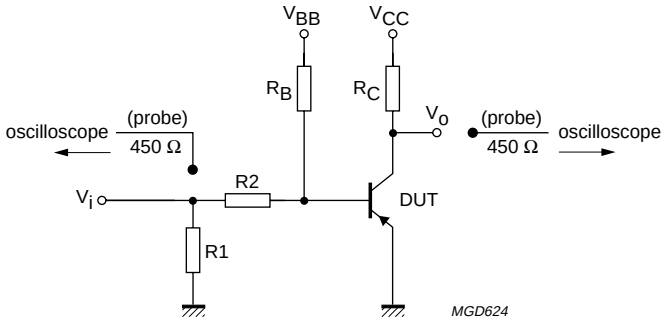
Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 6 cm^2. For other mounting conditions, see *"Thermal considerations for SOT89 in the General Part of associated Handbook".*

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = –50 V	–	–10	nA
		I_E = 0; V_{CB} = –50 V; T_{amb} = 125 °C	–	–10	µA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = –5 V	–	–50	nA
h_{FE}	DC current gain	I_C = –0.1 mA; V_{CE} = –1 V	75	–	
		I_C = –1 mA; V_{CE} = –1 V	100	–	
		I_C = –10 mA; V_{CE} = –1 V	100	–	
		I_C = –150 mA; V_{CE} = –2 V	100	300	
		I_C = –500 mA; V_{CE} = –10 V	50	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = –150 mA; I_B = –15 mA	–	–400	mV
		I_C = –500 mA; I_B = –50 mA	–	–1.6	V
V_{BEsat}	base-emitter saturation voltage	I_C = –150 mA; I_B = –15 mA	–	–1.3	V
		I_C = –500 mA; I_B = –50 mA	–	–2.6	V
C_c	collector capacitance	$I_E = i_e$ = 0; V_{CB} = –10 V; f = 1 MHz	–	8	pF
C_e	emitter capacitance	$I_C = i_c$ = 0; V_{EB} = –500 mV; f = 1 MHz	–	35	pF
f_T	transition frequency	I_C = –20 mA; V_{CE} = –10 V; f = 100 MHz	200	–	MHz
Switching times (between 10% and 90% levels); (see Fig.2)					
t_{on}	turn-on time	I_{Con} = –150 mA; I_{Bon} = –15 mA; I_{Boff} = 15 mA	–	40	ns
t_d	delay time		–	12	ns
t_r	rise time		–	30	ns
t_{off}	turn-off time		–	365	ns
t_s	storage time		–	300	ns
t_f	fall time		–	65	ns

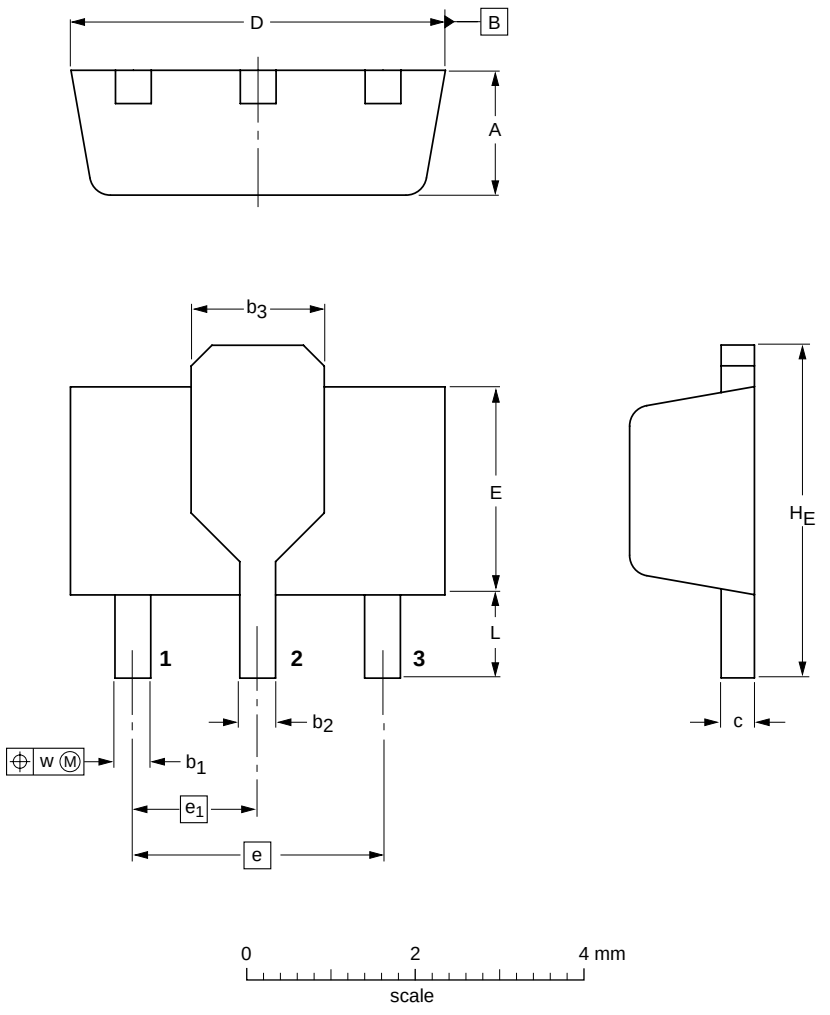


V_i = –9.5 V; T = 500 μs; t_p = 10 μs; $t_r = t_f \leq 3$ ns.
R1 = 68 Ω; R2 = 325 Ω; R_B = 325 Ω; R_C = 160 Ω.
V_{BB} = 3.5 V; V_{CC} = –29.5 V.
Oscilloscope input impedance Z_i = 50 Ω.

Fig.2 Test circuit for switching times.

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 3 leads **SOT89**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_1	b_2	b_3	c	D	E	e	e_1	H_E	L min.	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.37	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	0.8	0.13

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT89		TO-243	SC-62			~~97-02-28~~ 99-09-13

DATA SHEET STATUS

DATA SHEET STATUS[1]	PRODUCT STATUS[2]	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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Printed in The Netherlands 613514/04/pp8 Date of release: 2002 Mar 20 Document order number: 9397 750 09423

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